风光欣技术资料

S1623

—NPN silicon —

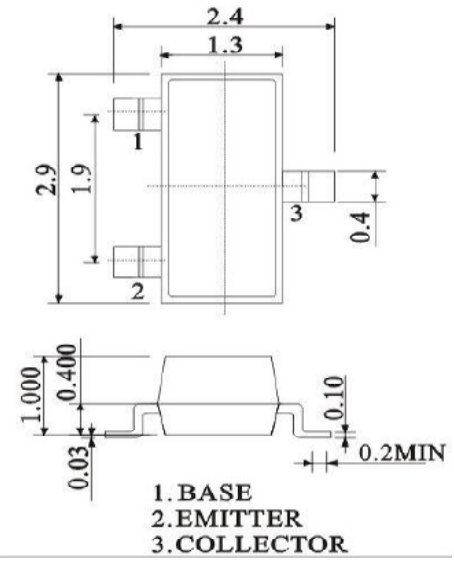
APPLICATION: GENERAL PURPOSE AMPLIFY APPLICATIONS,

WITCHING APPLICATION.

MAXIMUM RATINGS（Ta＝25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V_{CEO}	40	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_J	150	℃
Storage Temperature Range	Tstg	－55~150	℃

SOT-23



ELECTRICAL CHARACTERISTICS（Ta=25℃）

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	60		600		V_{CE}= 6V，Ic= 1mA
Collector Cut-off Current	I_{CBO}			0.1	μA	V_{CB}= 40V，I_E=0
Emitter Cut-off Current	I_{EBO}			0.1	μA	V_{EB}= 5V，Ic=0
Collector-Base Breakdown Voltage	BV_{CBO}	50			V	Ic= 0.1mA，I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	40			V	Ic= 1mA，I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	5			V	I_E= 0.1mA，Ic=0
Base-Emitte Voltage	V_{BE}			0.7	V	V_{CE}= 6V，Ic= 1mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.3	V	Ic= 100mA，I_B= 10mA
Base-Emitte Saturation Voltage	$V_{BE(sat)}$			1	V	Ic= 100mA，I_B= 10mA
Gain bandwidth product	f_T	200			MHz	Ic= 10mA，V_{CE}= 6V

h_{FE} **Classification And Marking**

Print Mark	SL3	SL4	SL5	SL6	SL7
Classification	L3	L4	L5	L6	L7
h_{FE}	60~90	90~135	135~200	200~400	400~600